

PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

INK0102AU1

High speed switching
Silicon N-channel MOSFET

DESCRIPTION

INK0102AU1 is a Silicon N-channel MOSFET.

This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low resistance.

FEATURE

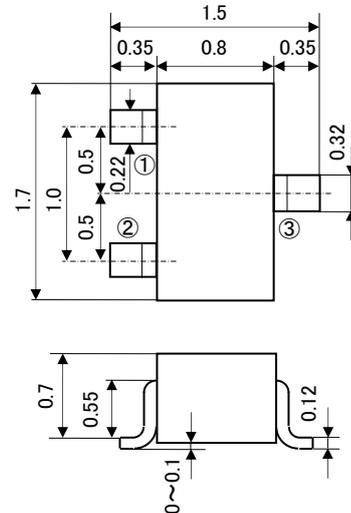
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage 2.5V
- Low on Resistance.
 $R_{DS(ON)}=0.35\ \Omega(TYP)$ @ $I_D=0.2A, V_{GS}=4.5V$
 $R_{DS(ON)}=0.48\ \Omega(TYP)$ @ $I_D=0.1A, V_{GS}=2.5V$
- High speed switching.
- Small packing for easy mounting.

APPLICATION

Inductive loads switching

OUTLINE DRAWING

Unit: mm



JEITA : SC-75A
JEDEC : -

TERMINAL CONNECTOR

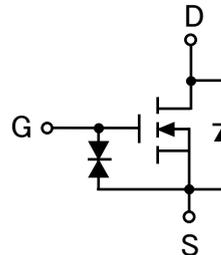
- ① : GATE
- ② : SOURCE
- ③ : DRAIN

MAXIMUM RATINGS (Ta=25°C)

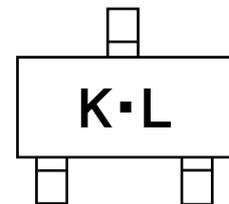
Symbol	Parameter	Rating	Unit
V _{DSS}	Drain-source voltage	30	V
V _{GS}	Gate-Source Voltage	±8	V
I _D	Drain Current(DC)	0.55	A
I _{DP}	Drain current(Pulse)	1.5(※1)	A
P _D	Total Power Dissipation	150	mW
T _{ch}	Channel Temperature	+150	°C
T _{stg}	Storage temperature	-55~+150	°C

※1 Single pulse $P_w \leq 10\ \mu s$, Duty cycle $\leq 1\%$

EQUIVALENT CIRCUIT



MARKING



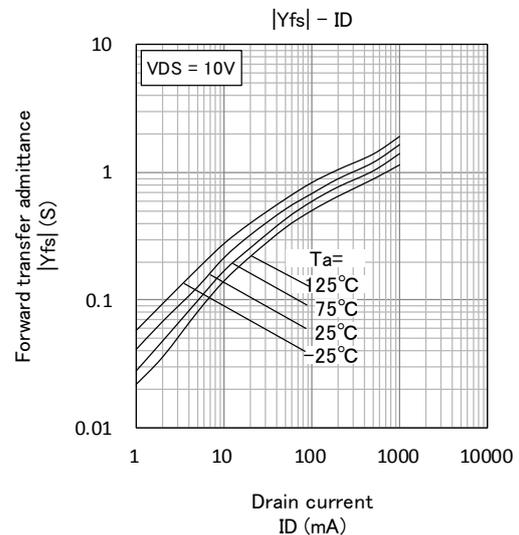
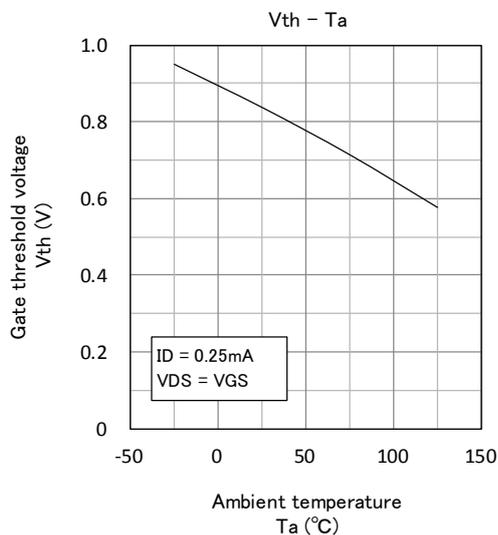
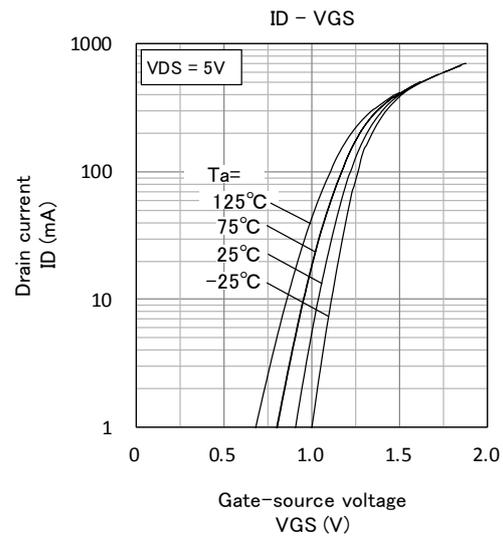
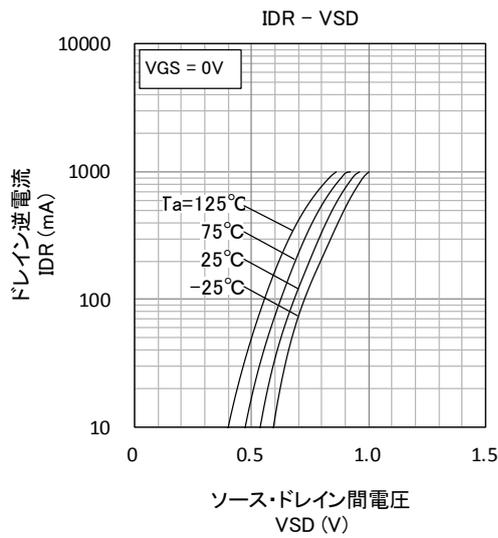
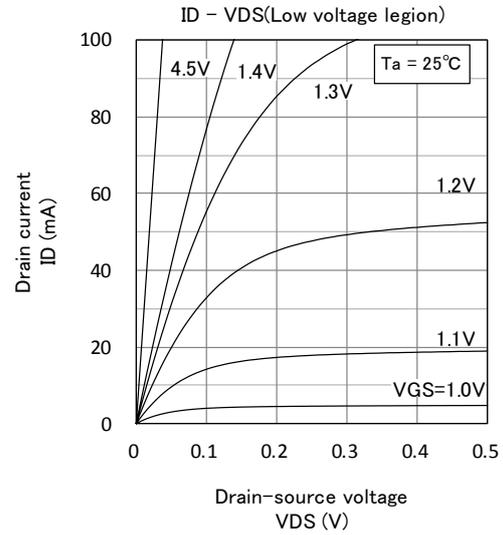
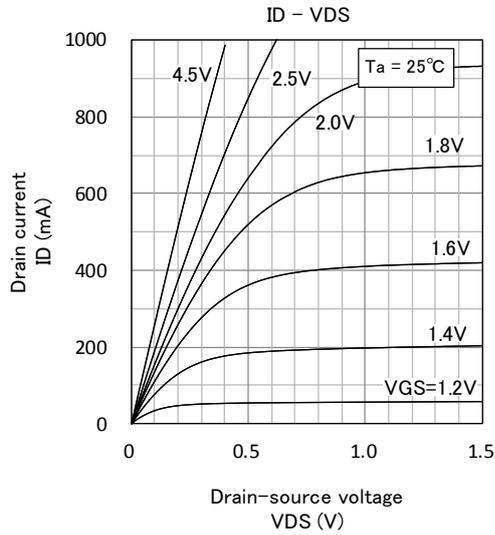
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =100μA, V _{GS} =0V	30	-	-	V
Gate-Source Leak current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	-	±10	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate Threshold Voltage	V _{th}	I _D =250μA, V _{DS} =V _{GS}	0.4	-	1.1	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =0.1A	-	700	-	mS
Static Drain-Source On-State Resistance	R _{DS(ON)}	I _D =0.2A, V _{GS} =4.5V	-	0.35	0.5	Ω
		I _D =0.1A, V _{GS} =2.5V	-	0.48	0.7	
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	62	-	pF
Output Capacitance	C _{oss}		-	10	-	
Switching Time	t _{on}	V _{DD} =10V, I _D =0.5A	-	23	-	ns
	t _{off}	V _{GS} =0~4.5V	-	28	-	

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TYPICAL CHARACTERISTICS

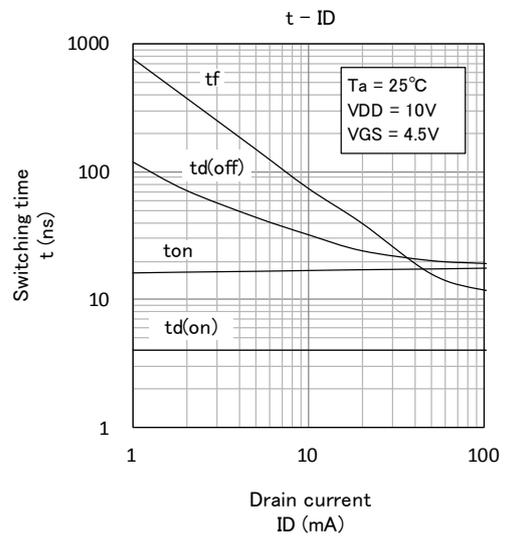
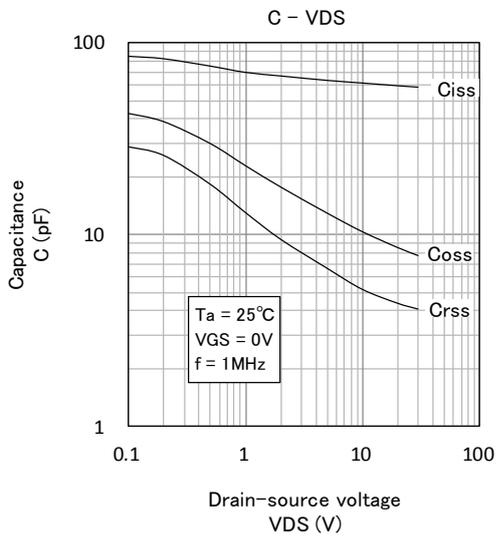
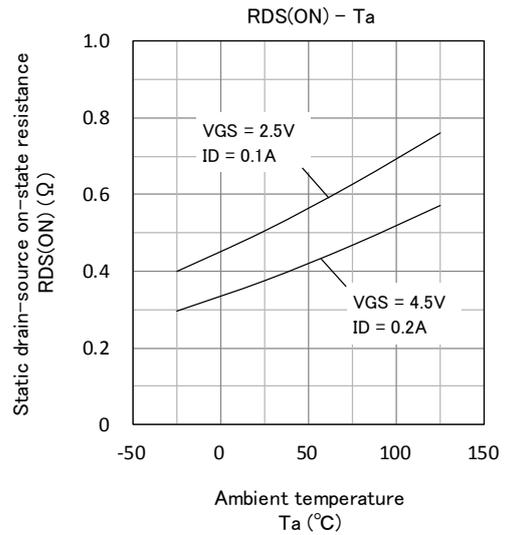
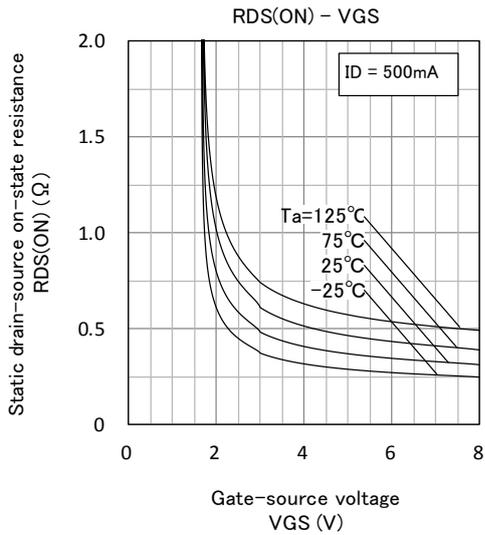
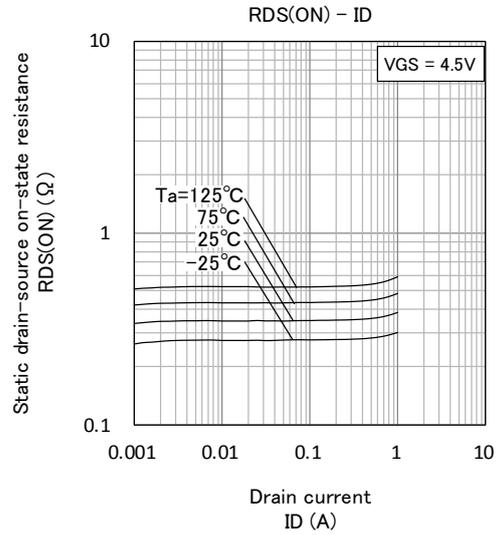
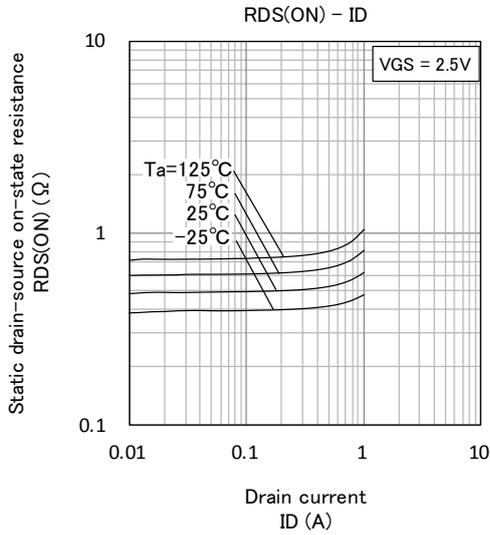


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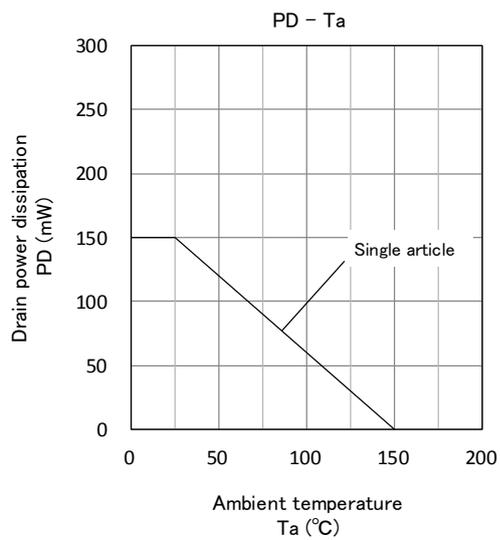
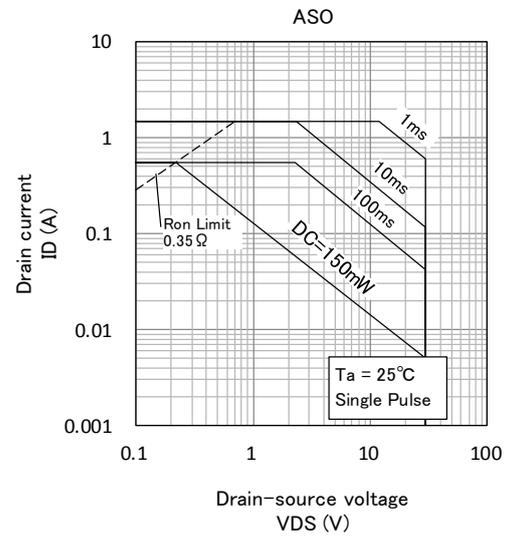
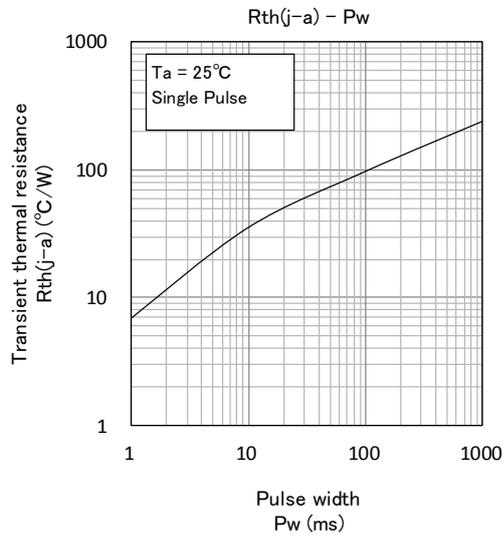


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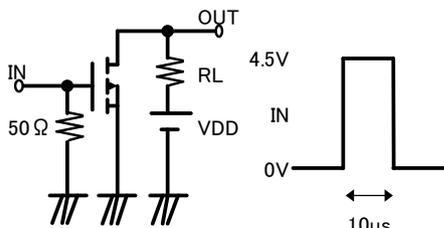
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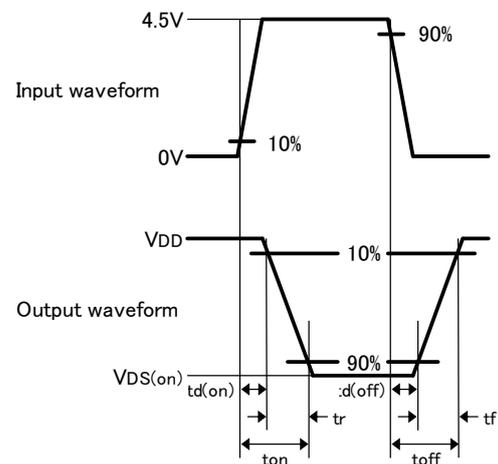
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Switching time test condition



Duty $\leq 1\%$
Input: $t_r, t_f < 10\text{ns}$
VDD = 10V
Common source
 $T_a = 25^\circ\text{C}$





Keep safety first in your circuit designs!

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